

**METHOD FOR POLYSILICON CONDUCTOR (PC) TRIMMING FOR  
SHRINKING CRITICAL DIMENSION AND ISOLATED-NESTED  
OFFSET CORRECTION**

**ABSTRACT**

5

A method of forming a semiconductor device, includes providing a structure having a first critical dimension, forming a lithographic pattern on the structure, and etching the structure with an O<sub>2</sub>-containing material to trim the first critical dimension to a second critical dimension, the second critical dimension being smaller than the first critical dimension. Thereafter, any offset between the nested features and the isolated feature can be corrected.